

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application.

**Listing of Claims:**

1. (Previously Presented) A Group III nitride substrate comprising:
  - a substrate;
  - a semiconductor layer formed on the substrate; and
  - Group III nitride crystals formed on the semiconductor layer,wherein the semiconductor layer is formed of a semiconductor expressed by a composition formula of  $\text{Al}_u\text{Ga}_v\text{In}_{1-u-v}\text{N}$  (wherein  $0 \leq u \leq 1$  and  $0 \leq v \leq 1$ ),
  - a surface of the semiconductor layer is a plane that is sloped in one direction and includes steps of (0001) planes arranged step-wise,
  - the plane that is sloped in one direction and the (0001) planes form an angle of at least  $0.05^\circ$  therebetween, and
  - the Group III nitride crystals formed on the semiconductor layer have variations in in-plane carrier concentration, the variations being within a range of one fifth to five times a carrier concentration mean value, and
  - the Group III nitride crystals have a dislocation density of  $1 \times 10^2 \text{ cm}^{-2}$  or lower.
2. (Original) The Group III nitride substrate according to claim 1, wherein the Group III nitride crystals are formed through liquid phase epitaxy.
3. (Previously presented) The Group III nitride substrate according to claim 1, wherein the plane sloped in one direction and the (0001) planes form an angle of  $0.05^\circ$  to  $0.5^\circ$  therebetween.

4. (Previously presented) The Group III nitride substrate according to claim 2, wherein surfaces of the Group III nitride crystals and the (0001) planes form an angle of  $0.05^\circ$  to  $5^\circ$  therebetween.

5. (Previously presented) The Group III nitride substrate according to claim 1, wherein the Group III nitride crystals are gallium nitride.

6. – 19. (Canceled)

20. (Currently Amended) A semiconductor device comprising:

a substrate according to claim 1; and

a semiconductor element formed on the substrate.

21. (Previously presented) The semiconductor device according to claim 20, wherein the semiconductor element is a laser diode or a light emitting diode.